## REMARKS

The Examiner has required restriction under 35 U.S.C. §121 between claims 33-61, drawn to a semiconductor device, classified in class 257, subclass 510, and claims 1-32, drawn to process for making semiconductor devices, classified in class 438, subclass 22+. Applicant hereby elects without traverse claims 1-32 for prosecution on the merits. Accordingly, claims 33-61 have been canceled without prejudice.

Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. The attached page(s) are captioned "**Version with markings to show changes made.**"

In view of the foregoing, allowance of claims 1-32 is requested. The Examiner is requested to phone the undersigned in the event that the next Office Action is one other than a Notice of Allowance. The undersigned is available for telephone consultation at any time during normal business hours (Pacific Time Zone).

Respectfully submitted,

Dated: October 26, 2001 By: _____

Frederick M. Fliegel, Ph.D.
Reg. No. 36,138

**Version with markings to show changes made**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Application Serial No. ..... 09/652,550
Filing Date .....August 31, 2000
Inventor .....Keiji Jono et al.
Assignee.....Micron Technology, Inc. and KMT Semiconductor, LTD
Group Art Unit.....2811
Examiner ..... T. Tran
Attorney's Docket No. .....KM1-001
Title: Methods of Forming an Isolation Trench in a Semiconductor, Methods of Forming an Isolation Trench in a Surface of a Silicon Wafer, Methods of Forming an Isolation Trench-Isolated Transistor, Trench-Isolated Transistor, Trench Isolation Structures Formed in a Semiconductor, Memory Cells and DRAMS

**37 CFR § 1.121(b)(1)(iii) AND 37 CFR § 1.121(c)(1)(ii) FILING REQUIREMENTS TO ACCOMPANY RESPONSE TO OCTOBER 12, 2001 OFFICE ACTION**

Deletions are bracketed, additions are underlined.

**In the Claims**

Claims 33-61 have been canceled.

**END OF DOCUMENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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**Washington, D.C. 20231**

**CERTIFICATE OF FACSIMILE TRANSMISSION UNDER 37 CFR 1.8**

I hereby certify that the following papers are being facsimile transmitted to the Patent and Trademark Office at **(703) 872-9318** on the date shown below:

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3. Response to 06/25/02 Teleconference With Examiner
4. Postcard which accompanied Response to 10/12/01 Office Action w/PTO receipt stamp
5. Transmittal Form dated 10/26/01 which accompanied said Response to 10/12/01 Office Action
6. Response to 10/12/01 Office Action
7. Version With Markings to Show Changes Made

Dated: 06/27/02

By: Pat Palmer
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**NUMBER OF PAGES IN FACSIMILE: 19**